

29. (Amended) A method of inducing a strain by a first element of porous crystalline silicon on a second element, the method comprising the steps of attaching to, or integrally forming with, the first element, the second element, and having at least one electrode being in electrical contact solely with the first element of the first and second elements, such that subjecting the first element to an electric potential via said at least one electrode results in a strain induced by the first element on the second element.

REMARKS

Reconsideration of the above identified application in view of this Amendment is respectfully requested. This Amendment is in response to the Office Action dated March 13, 2002. This response is based on the discussion during the telephone interview between the Attorney for Applicant, including attendance of the inventor, Dr. Erez Ribak, and, the Examiner, during which the Examiner agreed to Applicant's request for filing this Response

By said Office Action, the Examiner stated the following items:

Item 1: claims 29 - 31 were withdrawn from consideration as being directed to a non-elected invention, according to 37 CFR 1.142(b) and MPEP 821.03.

Item 2: the drawings were objected to under 37 CFR 1.83(a).

Item 3: claim 1 was rejected under 35 U.S.C. 102(e) as being anticipated by Takeuchi et al. (U.S. Patent No. 6,265,811 and Takeuchi hereinafter).

Item 4: claims 2 and 3 were rejected under 35 U.S.C. 103(a) as being unpatentable over Takeuchi in view of Seefeldt (U.S. Patent No. 6,021,675 and Seefeldt hereinafter).

By this Response, the Applicant has corrected 'obvious-to-correct' component reference number errors appearing in the text of the specification, on page 42, and, appearing in corresponding Figure 2. Formal drawings will be submitted at the time of paying the issue fee.